

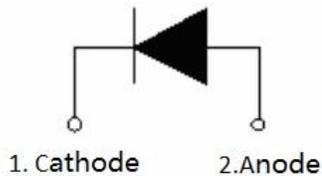
S4D30120H 1200V SIC POWER SCHOTTKY RECTIFIERS



Description

This 1200V 30A diode is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D30120H is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C TJ operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1200	V
Average Rectified Forward Current	$I_{F(AV)1}$	$T_C=25^\circ\text{C}$	114	A
	$I_{F(AV)2}$	$T_C=158^\circ\text{C}$	30	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, $T_C=25^\circ\text{C}$	300	A
	I_{FSM2}	10ms, Half Sine pulse, $T_C=110^\circ\text{C}$	246	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10ms, Half Sine pulse, $T_C=25^\circ\text{C}$	121	A
	I_{FRM2}	10ms, Half Sine pulse, $T_C=110^\circ\text{C}$	68	A
Power Dissipation	P_{tot1}	$T_C=25^\circ\text{C}$	441	W
	P_{tot1}	$T_C=110^\circ\text{C}$	191	W
I^2t Value	I^2t_1	10ms, $T_C=25^\circ\text{C}$	271	A ² s
	I^2t_2	10ms, $T_C=25^\circ\text{C}$	218	A ² s

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 30A, Pulse, $T_J = 25^\circ\text{C}$	1.5	1.8	V
	V_{F2}	@ 30A, Pulse, $T_J = 175^\circ\text{C}$	2.2	3.0	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25^\circ\text{C}$	1	20	μA
	I_{R2}	@ $V_R = \text{rated } V_R$, $T_J = 175^\circ\text{C}$	5	200	μA
Junction Capacitance	C_T	$V_R=1\text{V}$, $f=1\text{MHz}$, $T_J=25^\circ\text{C}$,	2581	-	pF
Reverse Recovery Charge	Q_c	$V_R = 800\text{V}$, $T_J=25^\circ\text{C}$	152	-	nC
Capacitance Stored Energy	E_c	$V_R = 800\text{V}$, $T_J=25^\circ\text{C}$	44	-	μJ

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.34	°C/W

Electrostatic Discharge (ESD) Classifications:

Parameter	Symbol	Value
Human Body Model	HBM	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

Ratings and Characteristics Curves

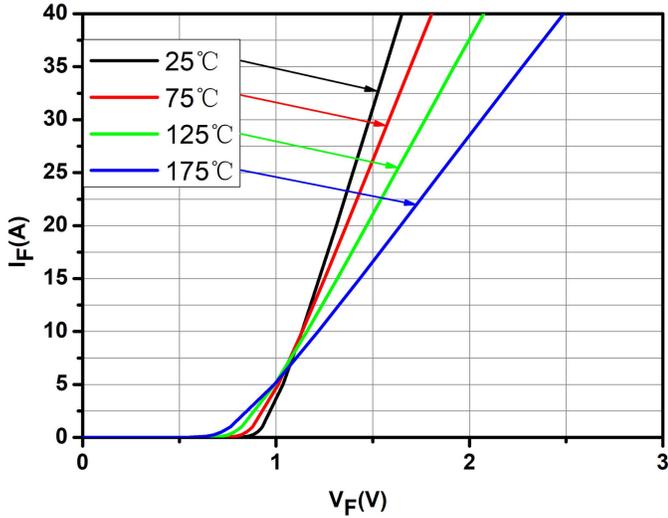


Fig.1-Typical Forward Voltage Characteristics

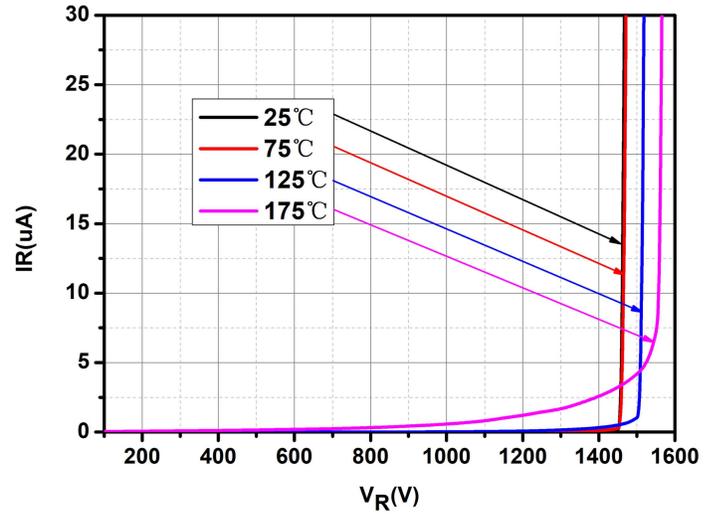


Fig.2-Typical Reverse Characteristics

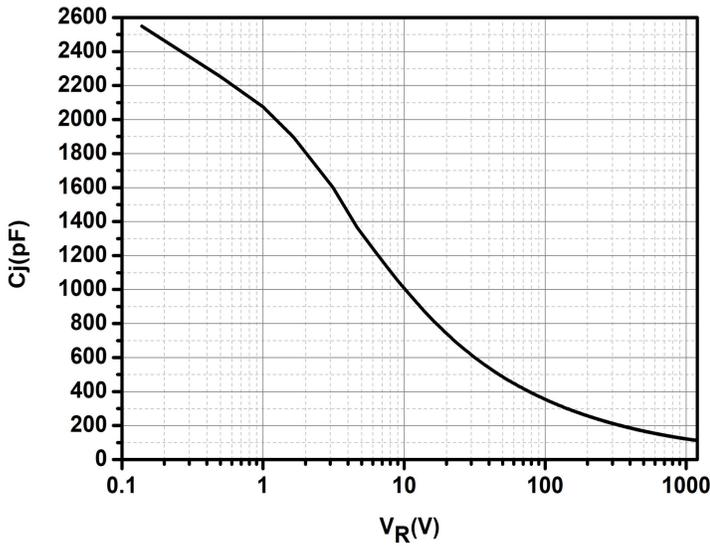


Fig.3-Capacitance vs. Reverse Voltage

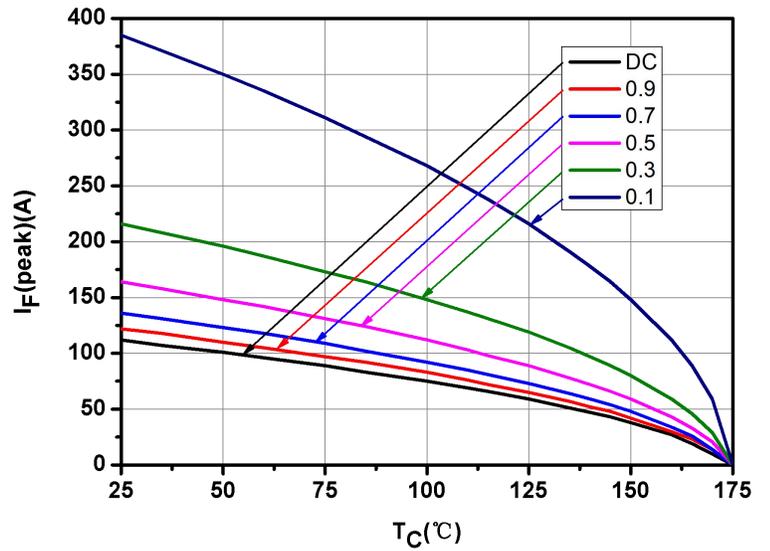


Fig.4-Current Derating

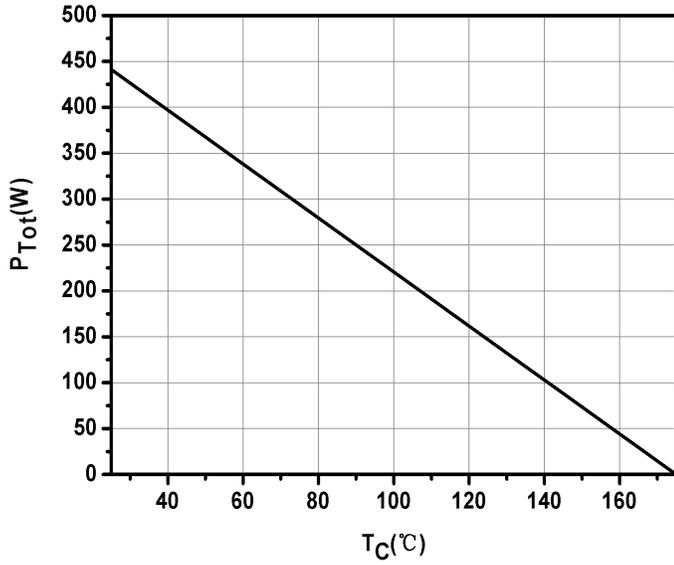


Fig.5-Power Derating

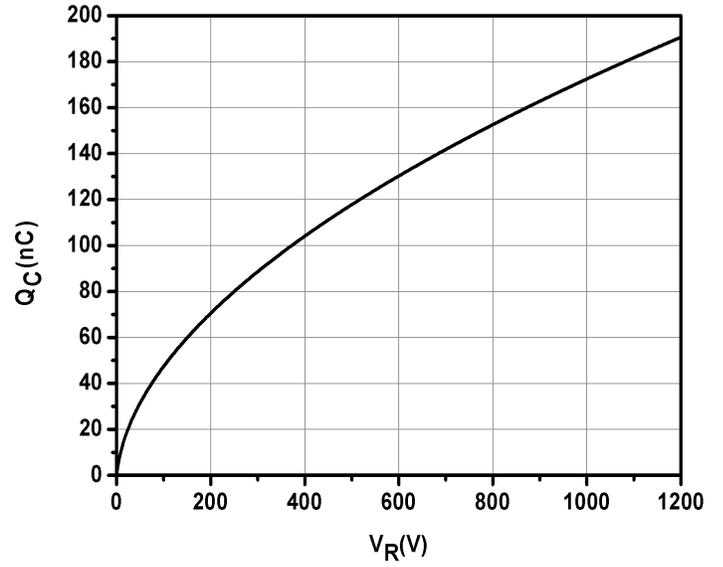


Fig.6-Total Capacitance Charge vs. Reverse Voltage

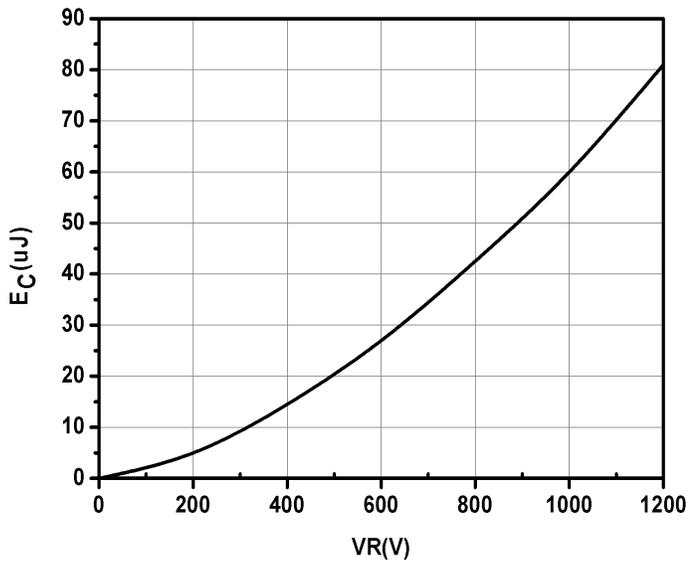
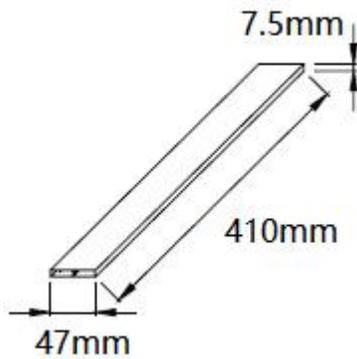


Fig.7-Capacitance Stored Energy

Ordering Information

Device	Package	Shipping
S4D30120H	TO-247AC(TO-247-2)	25pcs / tube

Tube Specification



Marking Diagram

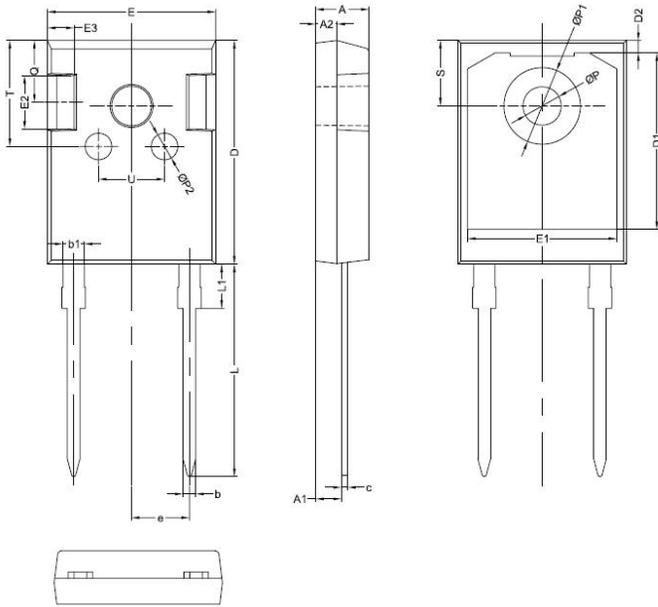


Where XXXXX is YYWWL

- S4D = Device Type
- H = Package type
- 30 = Forward Current (30A)
- 120 = Reverse Voltage (1200V)
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions : Molding resin
Epoxy resin UL : 94V-0

Mechanical Dimensions



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

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